NPN Epitaxial Planar Silicon Transistor



30C01S

Low-Frequency General-Purpose Amplifier Applications

Applications

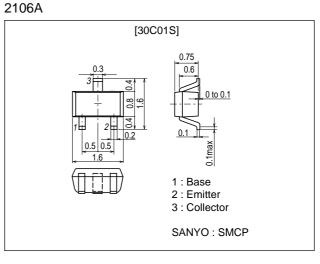
• Low-frequency Amplifier, muting circuit.

Features

- Large current capacitance.
- Low collector-to-emitter saturation voltage (resistance). $R_{CE}(sat)$ typ=0.70 Ω [IC=0.4A, IB=20mA].
- Ultrasmall package facilitates miniaturization in end products.
- Small ON-resistance (Ron).

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		40	V
Collector-to-Emitter Voltage	VCEO		30	V
Emitter-to-Base Voltage	VEBO		5	V
Collector Current	IC		400	mA
Collector Current (Pulse)	ICP		800	mA
Collector Dissipation	PC	Mounted on a glass epoxy board (20X30X1.6mm)	200	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
			min	typ	max	Unit	
Collector Cutoff Current	ІСВО	V _{CB} =30V, I _E =0			0.1	μΑ	
Emitter Cutoff Current	IEBO	VEB=4V, IC=0			0.1	μA	
DC Current Gain	hFE	V _{CE} =2V, I _C =10mA	300		800		
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =50mA		380		MHz	
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		2.4		pF	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	IC=100mA, IB=5mA		100	200	mV	
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=100mA, IB=5mA		0.9	1.2	V	
Arking · YO							

Marking : YQ

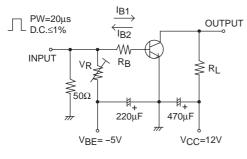
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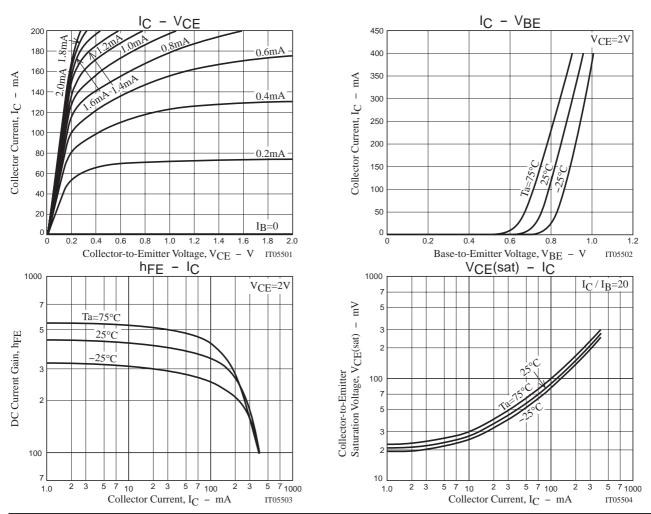
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

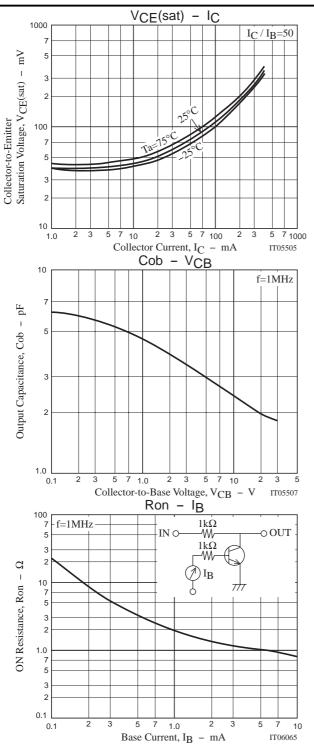
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0	40			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, R _{BE} =∞	30			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=10μA, IC=0	5			V
Turn-ON Time	ton	See specified Test Circuit.		42		ns
Storage Time	tstg	See specified Test Circuit.		135		ns
Fall Time	tf	See specified Test Circuit.		90		ns

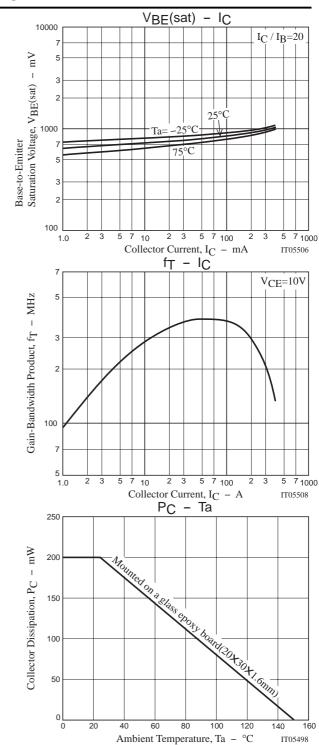
Switching Time Test Circuit



 $I_{C}=20I_{B1}=-20I_{B2}=300mA$







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